

Silicon NPN Power Transistors

2SD2296

DESCRIPTION

- With TO-3PN package
- High breakdown voltage

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

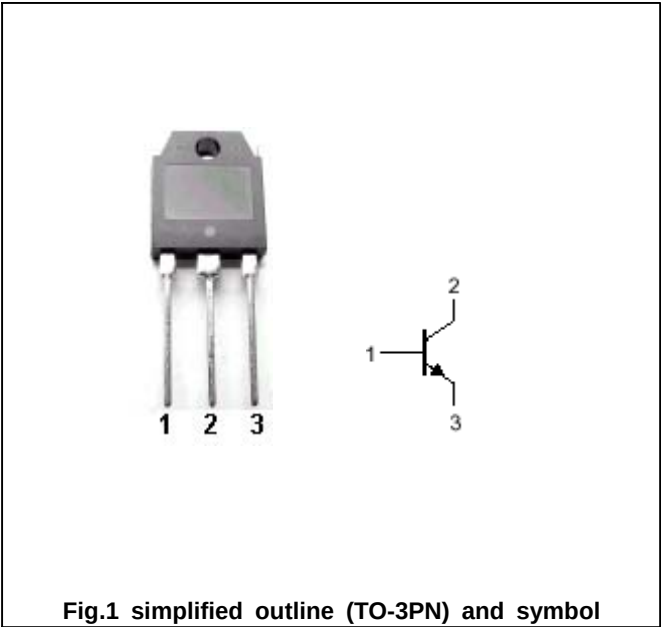


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current (DC)		5	A
I _{CP}	Collector current (Pulse)		6	A
P _C	Collector power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter breakdown voltage	I _C =10mA ;R _{BE} =∞	800			V
V _{EBO}	Emitter-base breakdown voltage	I _E =10mA ;I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.5A; I _B =1.2A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.5A; I _B =1.2A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =1500V ;R _{BE} =0			0.5	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	8		30	

Switching times

t _f	Fall time	I _C =4.0A I _{B1} =0.8A; I _{B2} ≈-1.5A			0.8	μs
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PACKAGE OUTLINE

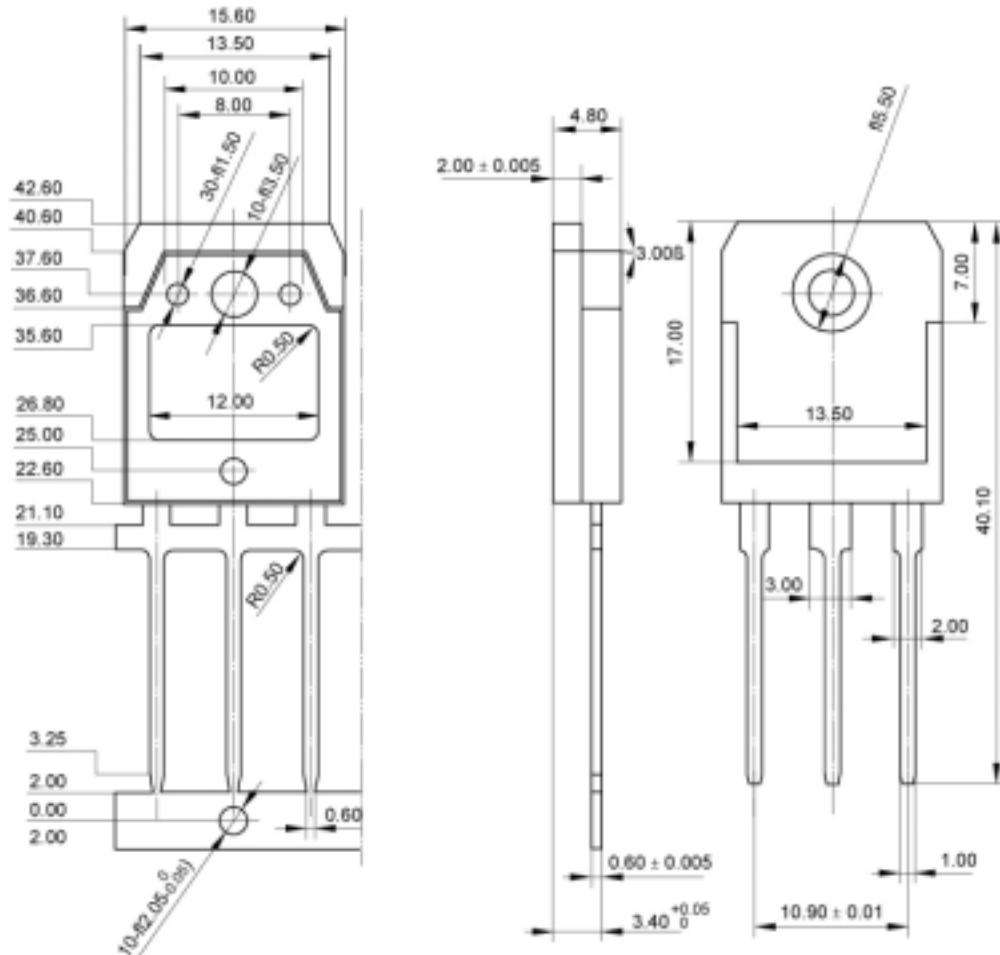


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)